CLAIMS

[Claim 1] A sputtering target containing 0.01 to 0.5 wt% of Ag, and remainder being W and unavoidable impurities, and a compositional variation of Ag in the target is less than 10%.

[Claim 2] The sputtering target according to claim 1, wherein the sputtering target has a structure configured from a W matrix phase and Ag grains, and Ag is not dissolved in the W matrix phase.

[Claim 3] The sputtering target according to claim 1 or claim 2, wherein an average grain size of the Ag grains is 0.1 to 10 μm.

[Claim 4] The sputtering target according to any one of claims 1 to 3, wherein the sputtering target has a purity of 99.999% or higher.

[Claim 5] A method of producing a sputtering target, wherein a W powder having an average grain size of 0.1 to 10 μm and a Ag powder having an average grain size of 0.1 to 10 μm are mixed to achieve a mix ratio of 0.01 to 0.5 wt% of Ag, and remainder being W and unavoidable impurities, and the mixed powder is sintered at a pressure of 15 to 30 MPa and a temperature of 1600 to 2000°C.